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| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. | |
|---|------------------|----------------------|-------------------------|------------------|--|
| 10/657,530 | 09/08/2003 | Leland S. Swanson | TI-33235.1 | 9171 | |
| 23494 7590 11/15/2004 EXAMINER | | | | | |
| TEXAS INSTRUMENTS INCORPORATED P O BOX 655474, M/S 3999 | | | ANYA, IGWE U | | |
| | DALLAS, TX 75265 | | ART UNIT | PAPER NUMBER | |
| | | | 2825 | ·· · | |
| | | | DATE MAILED: 11/15/2004 | 4 • • | |

Please find below and/or attached an Office communication concerning this application or proceeding.

| | | | | | UN |
|---|--|---|---|--|----------|
| | _ | Applica | tion No. | Applicant(s) | |
| Office Action Comments | | | 530 | SWANSON ET AL. | |
| Οπιсе | Action Summary | Examin | | Art Unit | |
| | | Igwe U. | • | 2825 | |
| The MAIL Period for Reply | ING DATE of this commun | ication appears on t | he cover sheet with the d | correspondence address | |
| THE MAILING D. - Extensions of time mafter SIX (6) MONTH - If the period for reply - If NO period for reply - Failure to reply within Any reply received by | STATUTORY PERIOD F ATE OF THIS COMMUN ay be available under the provisions S from the mailing date of this com specified above is less than thirty (3 is specified above, the maximum st the set or extended period for reply the Office later than three months a djustment. See 37 CFR 1.704(b). | CATION. of 37 CFR 1.136(a). In no nunication. 0) days, a reply within the s atutory period will apply and will, by statute, cause the a | event, however, may a reply be tir tatutory minimum of thirty (30) day will expire SIX (6) MONTHS from pplication to become ABANDONE | nely filed rs will be considered timely. Ithe mailing date of this communic (D (35 U.S.C. § 133). | cation. |
| Status | | | | | |
| 1)⊠ Responsiv | e to communication(s) file | ed on 24 August 20 | <u>04</u> . | | |
| 2a)⊠ This action | | 2b)□ This action is | | | , |
| | application is in condition ccordance with the practi | | • | | ts is |
| Disposition of Clair | ns | | | | |
| 4a) Of the a 5) | 3-40 is/are pending in the above claim(s) is/a 0 is/are allowed. 3.34 and 36-39 is/are rejections is/are objected to are subject to restrict | re withdrawn from o | | | |
| Application Papers | | | | | |
| 10)⊠ The drawing Applicant m Replacemen | cation is objected to by the g(s) filed on <u>08 Septembers</u> ay not request that any object that any objected to be declaration is objected to | <u>er 2003</u> is/are: a)⊠ ction to the drawing(s the correction is requ |) be held in abeyance. Se uired if the drawing(s) is ob | e 37 CFR 1.85(a). ejected to. See 37 CFR 1.1 | 21(d). |
| Priority under 35 U. | S.C. § 119 | | | | |
| 12) Acknowledg a) All b) Certi 2. Certi 3. Copi | gment is made of a claim Some * c) None of: ified copies of the priority ified copies of the priority es of the certified copies ication from the Internation ched detailed Office action | documents have be documents have be of the priority docur nal Bureau (PCT R | een received. een received in Applicat ments have been receive ule 17.2(a)). | ion No ed in this National Stage | ; |
| Attachment(s) | | | | | |
| | son's Patent Drawing Review (F ure Statement(s) (PTO-1449 or | | 4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other: | | |

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).
- 3. Claims 33, 34 and 37 are rejected under 35 U.S.C. 103(a) as being unpatentable over Schuegraf (US Patent 6620732) in view of Vanhaelemeersch et al. (US Patent 6599814).
- 4. Schuegraf '732 teaches a bipolar transistor, comprising a collector region (402), a base region (420) overlying the collector region, an emitter-base dielectric stack comprising a carbide layer (444) sandwiched between oxide layers (442, 446) and having an opening exposing the base region (figs. 3A), and an emitter poly layer (430, 330) overlying the emitter-base dielectric and an exposed portion of the dielectric. The

first oxide contacting the base comprises silicon oxide, the carbide layer comprises silicon carbide (col. 5 lines 52 - 67), and the second oxide comprises a silicon oxy nitride (col. 6 lines 12 - 31).

- 5. Schuegraf '732 does not disclose an oxide layer resistive to a carbide dry etching process overlying the carbide layer.
- 6. However, Vanhaelemeersch et al. teach an oxide layer (34, 44, & col. 5 lines 38 51) resistive to a carbide dry etching process (col. 10 line 62 col. 11 line 17) overlying a carbide layer (35, 45), and a base region (32, & col. 9 lines 64 col. 10 line 3) underlying the carbide layer for a large process window (col. 11 lines 3 5). Vanhaelemeersch et al., further disclose that silicon carbide underlying layer (43) can also be a stack of non-conductive barrier layer on a conductive layer (col. 10 lines 45 52), and a carbide layer of about 500 angstroms (col. 10 lines 38 41).
- 7. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the teachings of Vanhaelemeersch et al. into the Schuegraf '732 references to achieve a large process window that is self aligned.
- 8. Claims 36, 38, and 39 are rejected under 35 U.S.C. 103(a) as being in view of Vanhaclemeersch etal and further in unpatentable over Schuegraf (US Patent 6620732) in view of Schuegraf (US Patent 6444535).
- 9. Schuegraf '732/ Vanhaelemeersch et al. reference teaches the features previously outlined, but lacks the thickness of the first oxide ranging from 70 100 angstroms, the first silicon oxide being a composite of a thermal silicon oxide 20 50

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angstroms thick and a deposited silicon oxide of about 50 angstroms thereover, the silicon carbide having a thickness of about 100 angstroms, and the second oxide layer being silicon oxide of thickness 500 – 1000 angstroms.

- 10. However, Schuegraf '535 teaches a first silicon oxide of thickness 80 – 500 angstroms (col. 5 lines 47 – 57), and a silicon carbide of thickness 500 – 1000 angstroms (col. 5 line 58 – col. 6 line 2) for proper control of the emitter width. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teachings of the Schuegraf '535 with the Schuegraf '732/ Vanhaelemeersch et al. reference for proper control of critical dimension. Where the general conditions of a claim are disclosed in prior art discovering the optimum or working ranges involves only routine skill in the art. In re Aller, 105 USPQ 233.
- 11. Art made of record and not relied upon considered pertinent to applicant's disclosure include Chuang et al. (US 2003/0096486).
- 12. Claim 35 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 13. Claim 40 is allowable inter alia: a first oxide layer comprising a deposited silicon oxide layer overlying a thermal silicon oxide layer.

Remarks

14... The examiner has reviewed prior art in light of applicant's comments and amendment and finds it persuasive as to a first oxide layer comprising a deposited silicon oxide layer overlying a thermal silicon oxide layer. Applicant's argument

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regarding an oxide layer resistive to a carbide dry etching process is unpersuasive, because etching selectivity is dependent upon the etchant chemistry relative to the etched substrates. Examiner also has discovered a new reference that teaches an oxide layer resistive to a carbide dry etching process. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, THIS ACTION IS MADE FINAL. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Contact Information

15. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Igwe U. Anya whose telephone number is (571) 272-1887. The examiner can normally be reached on M - F 8:30am - 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on (571) 272-1907. The fax phone

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number for the organization where this application or proceeding is assigned is 703-

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872-9306.

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Business Center (EBC) at 866-217-9197 (toll-free).

Igwe U. Anya Examiner Art Unit 2825

IA

November 3, 2004

SUPERVISORY PATENT EXAMINER

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